LMK1C110x 1.8V、2.5V 和 3.3V LVCMOS 时钟缓冲器系列

1 特性

- 高性能 1:4 LVCMOS 时钟缓冲器
- 输出偏斜极低，< 50ps
- 附加抖动极低，最大值 < 50fs
  - V_{DD} = 3.3V 时，典型值为 7.5fs
  - V_{DD} = 2.5V 时，典型值为 10fs
  - V_{DD} = 1.8V 时，典型值为 19.2fs
- 传播延迟极低，< 3ns
- 同步输出使能
- 电源电压：3.3V、2.5V 或 1.8V
  - 在电源电压范围内输入端耐受 3.3V 电压
- f_{max} = 250MHz (3.3V)
  f_{max} = 200MHz（2.5V 和 1.8V）
- 工作温度范围：–40°C 至 125°C
- 采用 8 引脚 TSSOP 封装

2 应用

- 工厂自动化与控制
- 电信设备
- 数据中心和企业计算
- 电网基础设施
- 电机驱动
- 医疗成像

3 说明

LMK1C110x 是德州仪器 (TI) 的一款模块化、高性能、低偏斜、通用时钟缓冲器系列器件。

整个系列采用模块化方法设计。

该系列所有器件均互相引脚兼容，并与 CDCLVC110x 系列向后兼容，从而易于处理。

该系列所有器件均具有相同的高性能特性，如低附加抖动、低偏斜和宽工作温度范围。

LMK1C110x 具有同步输出使能控制端 (1G)，可在 1G 处于低电平时将输出切换为低电平状态。

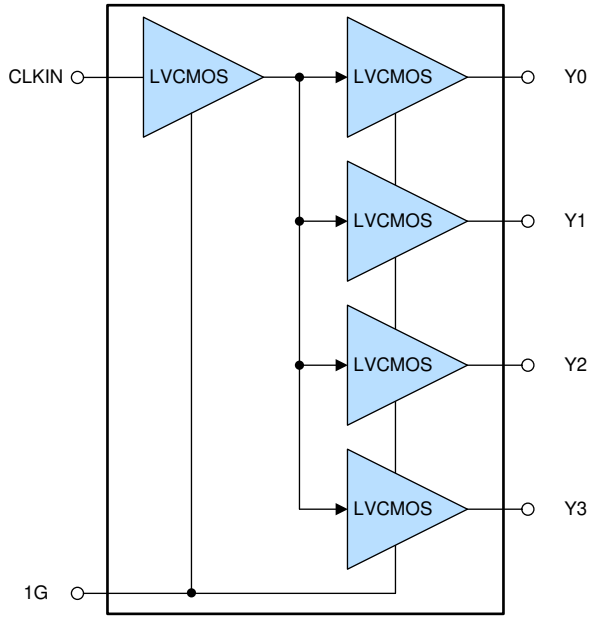
LMK1C110x 系列可在 1.8V、2.5V 和 3.3V 电压下工作，额定工作温度范围为 –40°C 至 125°C。

器件信息(1)

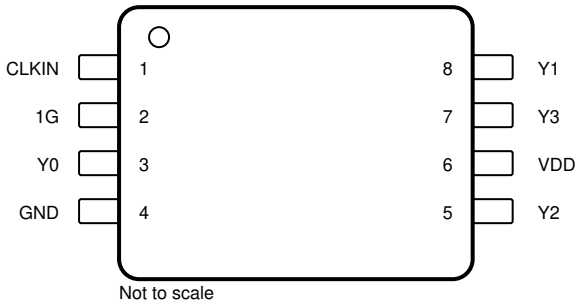
器件型号	封装	封装尺寸（标称值）
LMK1C1104PW	TSSOP (8)	3.00mm × 4.40mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

功能方框图



引脚分配



Not to scale

目录

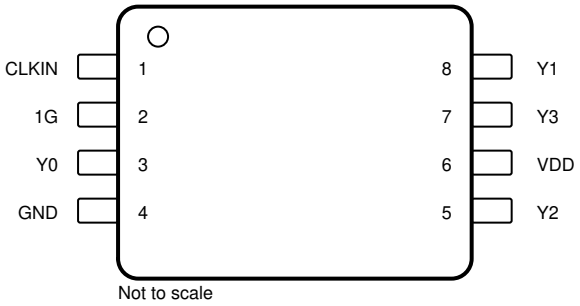
4 修订历史记录

Changes from Original (Decmeber 2019) to Revision A **Page**

- 向数据表添加了 LMK1C1102 和 LMK1C1103 ... 1
- Changed G1 pin description ... 3
- Changed VDD pin description ... 3
- Changed the *Power Supply Recommendations* section ... 11

5 Pin Configuration and Functions

PW Package
8-Pin TSSOP
Top View



Not to scale

Pin Functions

PIN		TYPE	DESCRIPTION
NAME	LMK1C1104		
LVCMOS CLOCK INPUT			
CLKIN	1	Input	Single-ended clock input with internal 300-kΩ (typical) pulldown resistor to GND. Typically connected to a single-ended clock input.
CLOCK OUTPUT ENABLE			
1G	2	Input	Global Output Enable with internal 300-kΩ (typical) pulldown resistor to GND. Typically connected to VDD with external pullup resistor. HIGH: outputs enabled LOW: outputs disabled
LVCMOS CLOCK OUTPUT			
Y0	3	Output	LVCMOS output. Typically connected to a receiver. Unused outputs can be left floating.
Y1	8		
Y2	5		
Y3	7		
SUPPLY VOLTAGE			
VDD	6	Power	Power supply terminal. Typically connected to a 3.3-V, 2.5-V, or 1.8-V supply. The VDD pin is typically connected to an external 0.1-μF capacitor near the pin.
GROUND			
GND	4	GND	Power supply ground.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V_{DD}	Supply voltage	–0.5	3.6	V
V_{CLKIN}	Input voltage (CLKIN)			
V_{IN}	Input voltage (1G)			
V_{Yn}	Output pins (Yn)	–0.5	V_{DD} + 0.3	
I_{IN}	Input current	–20	20	mA
I_O	Continuous output current	–50	50	mA
T_{stg}	Storage temperature	–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±6000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_{DD}	Core supply voltage	3.3-V supply	3.135	3.3	3.465	V
		2.5-V supply	2.375	2.5	2.625	
		1.8-V supply	1.71	1.8	1.89	
T_A	Operating free-air temperature		–40		125	°C
T_J	Operating junction temperature		–40		150	°C

6.4 Thermal Information

THERMAL METRIC(1)		LMK1C1104 PW (TSSOP) 8 PINS	UNIT
R_{qJA}	Junction-to-ambient thermal resistance	181.9	°C/W
$R_{qJC(top)}$	Junction-to-case (top) thermal resistance	76.6	°C/W
R_{qJB}	Junction-to-board thermal resistance	111.6	°C/W
Y_{JT}	Junction-to-top characterization parameter	16	°C/W
Y_{JB}	Junction-to-board characterization parameter	110.1	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

VDD = 3.3 V ± 5 %, –40°C ≤ TA ≤ 125°C. Typical values are at VDD = 3.3 V, 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CURRENT CONSUMPTION						
I_{DD}	Core supply current, static	All-outputs disabled, f_{IN} = 0 V		25	45	µA

Electrical Characteristics (continued)

VDD = 3.3 V ± 5 %, –40°C ≤ TA ≤ 125°C. Typical values are at VDD = 3.3 V, 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{DD}	Core supply current	All-outputs disabled, f_{IN} = 100 MHz		8	15	mA
		All-outputs active, f_{IN} = 100 MHz, C_L = 5pF, V_{DD} = 1.8 V		14	20	
		All-outputs active, f_{IN} = 100 MHz, C_L = 5pF, V_{DD} = 2.5 V		21	30	
		All-outputs active, f_{IN} = 100 MHz, C_L = 5pF, V_{DD} = 3.3 V		33	40	
CLOCK INPUT						
f_{IN_SE}	Input frequency	V_{DD} = 3.3 V	DC		250	MHz
		V_{DD} = 2.5 V and 1.8 V	DC		200	
V_{IH}	Input high voltage		0.7 x V_{DD}			V
V_{IL}	Input low voltage				0.3 x V_{DD}	
dV_{IN}/dt	Input slew rate	20% - 80% of input swing	0.1			V/ns
I_{IN_LEAK}	Input leakage current		–50		50	uA
C_{IN_SE}	Input capacitance	at 25°C		7		pF
CLOCK OUTPUT FOR ALL V_{DD} LEVELS						
f_{OUT}	Output frequency	V_{DD} = 3.3 V			250	MHz
		V_{DD} = 2.5 V and 1.8 V			200	
ODC	Output duty cycle	With 50% duty cycle input	45		55	%
t_{START}	Start-up time before output is active	See (1)			3	ms
t_{1G_ON}	Output enable time	See (2)			5	cycles
t_{1G_OFF}	Output disable time	See (3)			5	cycles
CLOCK OUTPUT FOR V_{DD} = 3.3 V ± 5%						
V_{OH}	Output high voltage	I_{OH} = 1 mA	2.8			V
V_{OL}	Output low voltage	I_{OL} = 1 mA			0.2	
$t_{RISE-FALL}$	Output rise and fall time	20/80%, C_L= 5 pF, fIN = 156.25 MHz		0.35	0.7	ns
$t_{OUTPUT-SKEW}$	Output-output skew	See (4)		25	50	ps
$t_{PART-SKEW}$	Part-to-part skew				450	
$t_{PROP-DELAY}$	Propagation delay	See (5)		1.5	2	ns
$t_{JITTER-ADD}$	Additive Jitter	f_{IN} = 156.25 MHz, Input slew rate = 2 V/ns, Integration range = 12 kHz - 20 MHz		8	20	fs, RMS
R_{OUT}	Output impedance			50		Ω
CLOCK OUTPUT FOR V_{DD} = 2.5 V ± 5%						
V_{OH}	Output high voltage	I_{OH} = 1 mA	0.8 x V_{DD}			V
V_{OL}	Output low voltage	I_{OL} = 1 mA			0.2 x V_{DD}	
$t_{RISE-FALL}$	Output rise and fall time	20/80%, C_L= 5 pF, f_{IN} = 156.25 MHz		0.33	0.8	ns
$t_{OUTPUT-SKEW}$	Output-output skew	See (4)			50	ps
$t_{PART-SKEW}$	Part-to-part skew				400	
$t_{PROP-DELAY}$	Propagation delay	See (5)		1.5	2.5	ns
$t_{JITTER-ADD}$	Additive Jitter	f_{IN} = 156.25 MHz, Input slew rate = 2 V/ns, Integration range = 12 kHz - 20 MHz		11	27	fs, RMS

(1) Measured from VDD stable to output active, when 1G = HIGH.
(2) Measured from 1G rising edge crossing VIH to first rising edge of Yn.
(3) Measured from 1G falling edge crossing VIL to last falling edge of Yn.
(4) Measured from rising edge of any Yn output to any other Ym output.
(5) Measured from rising edge of CLKIN to any Yn output.

Electrical Characteristics (continued)

VDD = 3.3 V ± 5 %, –40°C ≤ TA ≤ 125°C. Typical values are at VDD = 3.3 V, 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
R_{OUT}	Output impedance			52.5		Ω
CLOCK OUTPUT FOR V_{DD} = 1.8 V ± 5%						
V_{OH}	Output high voltage	I_{OH} = 1 mA	0.8 x V_{DD}			V
V_{OL}	Output low voltage	I_{OL} = 1 mA			0.2 x V_{DD}	V
$t_{RISE-FALL}$	Output rise and fall time	20/80%, C_L= 5 pF, f_{IN} = 156.25 MHz		0.38	1	ns
$t_{OUTPUT-SKEW}$	Output-output skew	See (4)			50	ps
$t_{PART-SKEW}$	Part-to-part skew				900	ps
$t_{PROP-DELAY}$	Propagation delay	See (5)		1.5	3	ns
$t_{JITTER-ADD}$	Additive Jitter	f_{IN} = 156.25 MHz, Input slew rate = 2 V/ns, Integration range = 12 kHz - 20 MHz		17.5	50	fs, RMS
R_{OUT}	Output impedance			60		Ω
GENERAL PURPOSE INPUT (1G)						
V_{IH}	High-level input voltage		0.75 x V_{DD}			V
V_{IL}	Low-level input voltage				0.25 x V_{DD}	V
I_{IH}	Input high-level current	V_{IH} = V_{DD_REF}	–50		50	µA
I_{IL}	Input low-level current	V_{IL} = GND	–50		50	µA

6.6 Timing Requirements

VDD = 3.3 V ± 5 %, –40°C ≤ TA ≤ 125°C

			MIN	NOM	MAX	UNIT
POWER SUPPLY						
V/t_{RAMP}	V_{DD} ramp rate		0.1		50	V/ms

6.7 Typical Characteristics

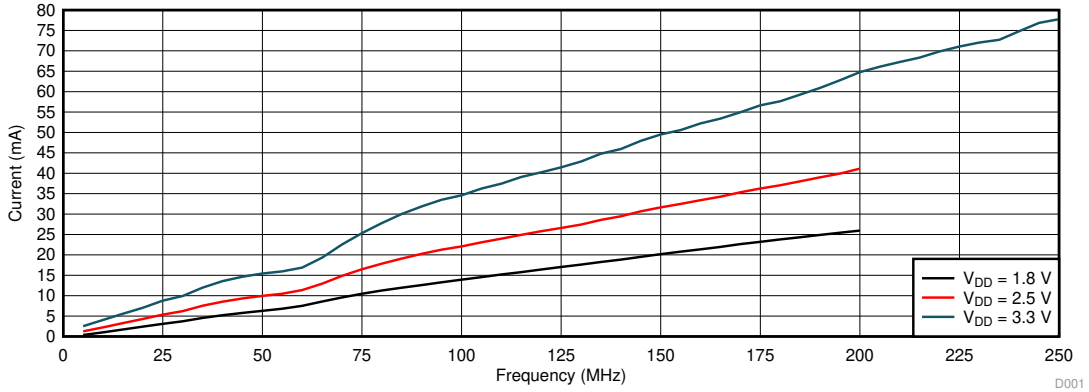


图 1. Device Power Consumption vs Clock Frequency (Load 5 pF)

7 Parameter Measurement Information

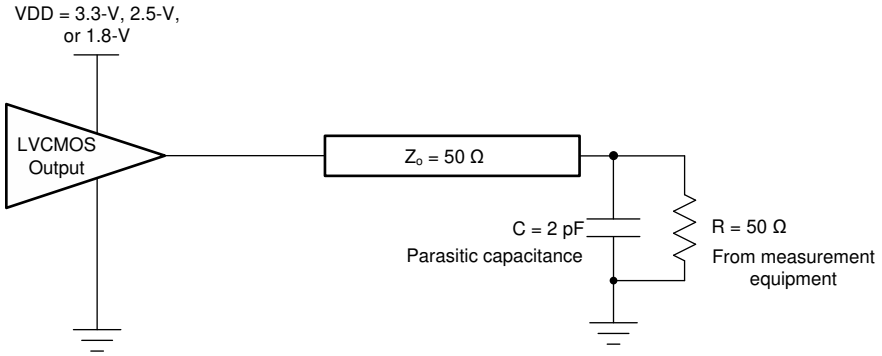


图 2. Test Load Circuit

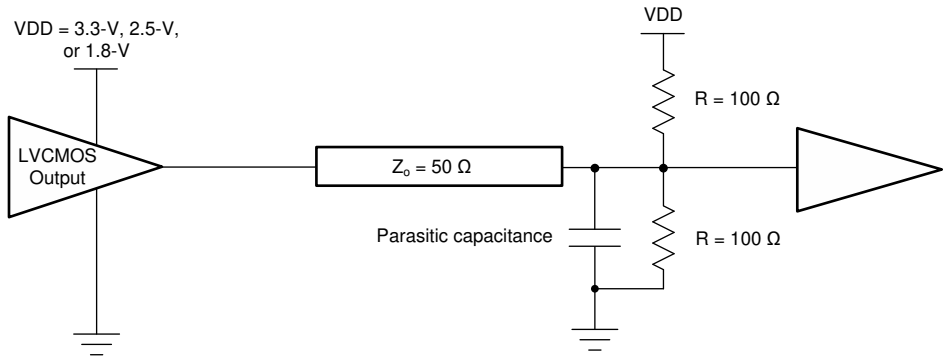


图 3. Application Load With 50-Ω Termination

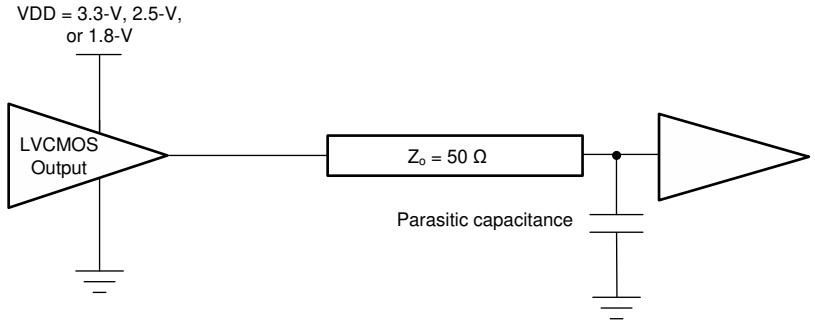


图 4. Application Load With Termination

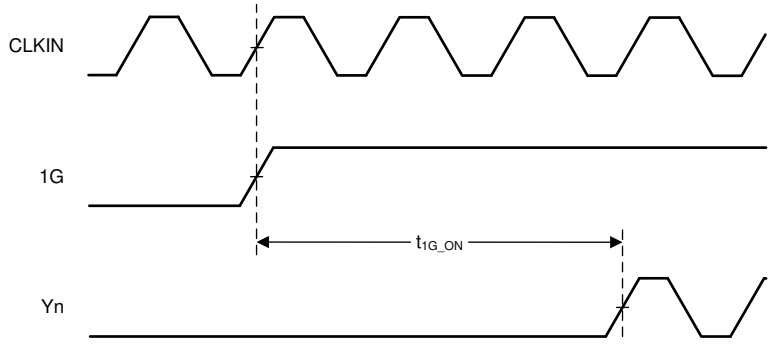


图 5. t_{1G_ON} Output Enable Time

Parameter Measurement Information (接下页)

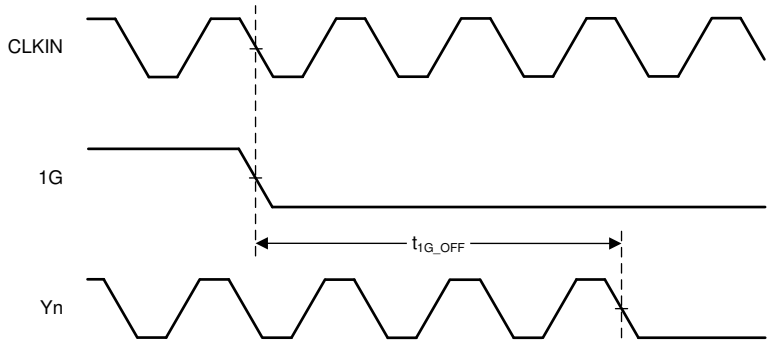


图 6. t_{1G_OFF} Output Disable Time

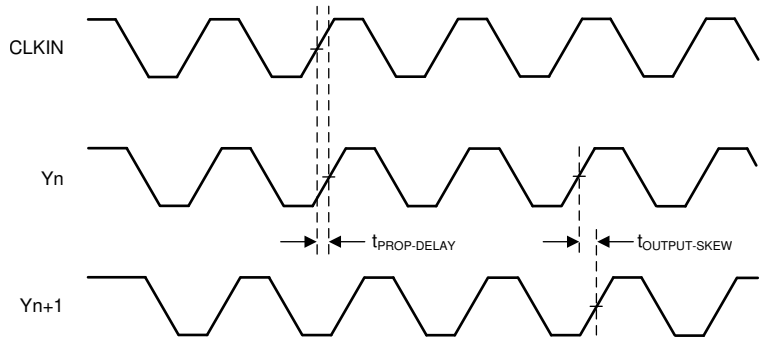


图 7. Propagation Delay $t_{PROP-DELAY}$ and Output Skew $t_{OUTPUT-SKEW}$

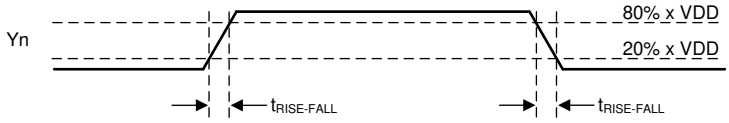


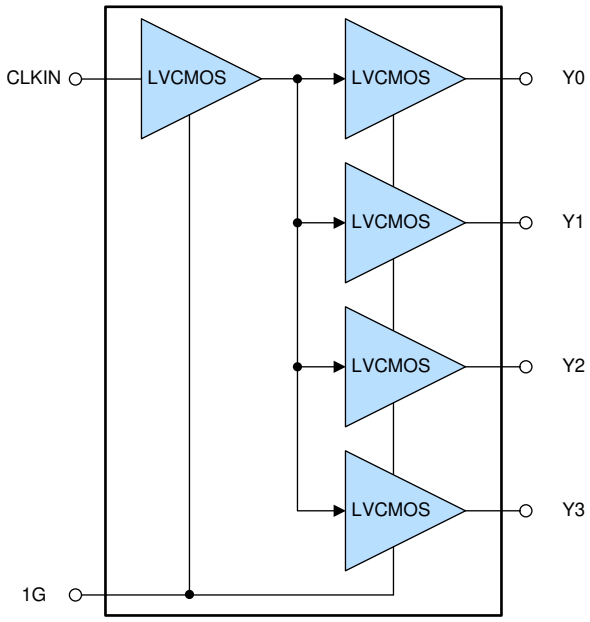
图 8. Rise and Fall Time $t_{RISE-FALL}$

8 Detailed Description

8.1 Overview

The LMK1C110x family of devices is part of a low-jitter and low-skew LVCMOS fan-out buffer solution. For best signal integrity, it is important to match the characteristic impedance of the LMK1C110x's output driver with that of the transmission line.

8.2 Functional Block Diagram



8.3 Feature Description

The outputs of the LMK1C110x can be disabled by driving the synchronous output enable pin (1G) low. Unused output can be left floating to reduce overall system component cost. Supply and ground pins must be connected to V_{DD} and GND, respectively.

8.4 Device Functional Modes

The LMK1C110x operates from 1.8-V, 2.5-V, or 3.3-V supplies. 表 1 shows the output logics of the LMK1C110x.

表 1. Output Logic Table

INPUTS		OUTPUTS
CLKIN	1G	Yn
X	L	L
L	H	L
H	H	H

9 Application and Implementation

> **注**
>
> Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LMK1C110x family is a low additive jitter LVCMOS buffer solution that can operate up to 250-MHz at V_{DD} = 3.3 V and 200 MHz at V_{DD} = 2.5 V to 1.8 V. Low output skew as well as the ability for synchronous output enable is featured to simultaneously enable or disable buffered clock outputs as necessary in the application.

9.2 Typical Application

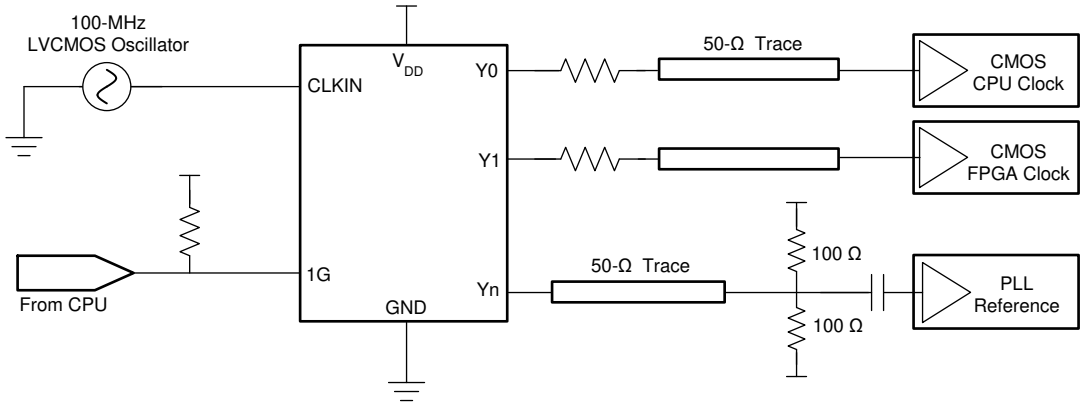


图 9. System Configuration Example

9.2.1 Design Requirements

The LMK1C110x shown in 图 9 is configured to fan out a 100-MHz signal from a local LVCMOS oscillator. The CPU is configured to control the output state through 1G.

The configuration example is driving three LVCMOS receivers in a backplane application with the following properties:

- The CPU clock can accept a full swing DC-coupled LVCMOS signal. A series resistor is placed near the LMK1C110x to closely match the characteristic impedance of the trace to minimize reflections.
- The FPGA clock is similarly DC-coupled with an appropriate series resistor placed near the LMK1C110x.
- The PLL in this example can accept a lower amplitude signal, so a Thevenin's equivalent termination is used. The PLL receiver features internal biasing, so AC coupling can be used when common-mode voltage is mismatched.

9.2.2 Detailed Design Procedure

Unused outputs can be left floating. See the *Power Supply Recommendations* section for recommended filtering techniques.

9.2.3 Application Curves

The low additive jitter of the LMK1C110x is shown in 图 10.

图 11 shows the low-noise 156.25-MHz reference source with 25.6-fs RMS jitter driving the LMK1C110x, resulting in 26.7-fs RMS jitter when integrated from 12 kHz to 20 MHz at 3.3-V supply. The resultant additive jitter measured is a low 7.6-fs RMS for this configuration.

Typical Application (接下页)

图 12 shows the low-noise 156.25-MHz reference source with 25.6-fs RMS jitter driving the LMK1C110x, resulting in 27.5-fs RMS jitter when integrated from 12 kHz to 20 MHz at 2.5-V supply. The resultant additive jitter measured is a low 10-fs RMS for this configuration.

图 13 shows the low-noise 156.25-MHz reference source with 25.6-fs RMS jitter driving the LMK1C110x, resulting in 32-fs RMS jitter when integrated from 12 kHz to 20 MHz at 1.8-V supply. The resultant additive jitter measured is a low 19.2-fs RMS for this configuration.

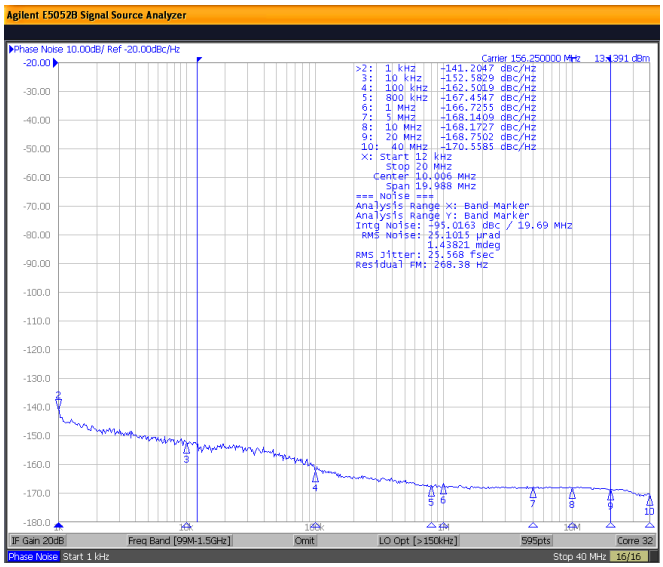


图 10. LMK1C110x Reference Phase Noise 25.6-fs (12 kHz to 20 MHz)

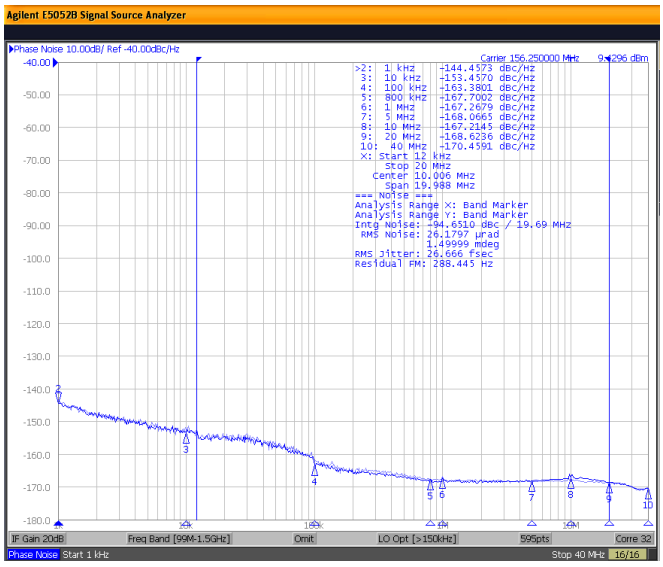


图 11. LMK1C110x 3.3-V Output Phase Noise 26.7-fs (12 kHz to 20 MHz)

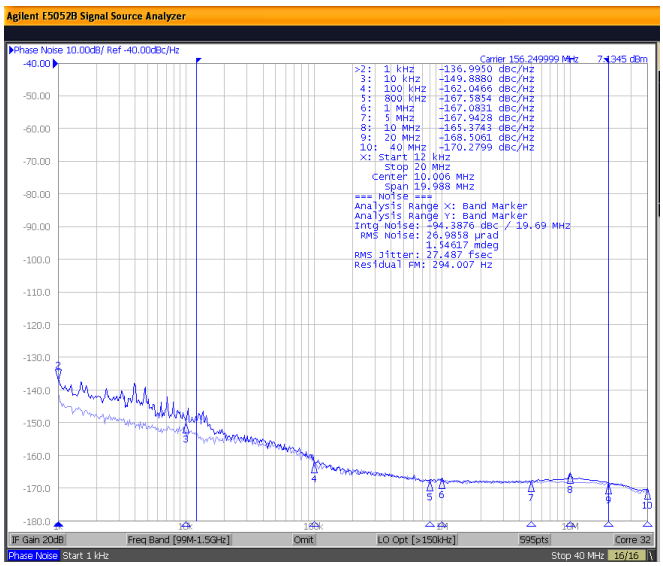


图 12. LMK1C110x 2.5-V Output Phase Noise 27.5-fs (12 kHz to 20 MHz)

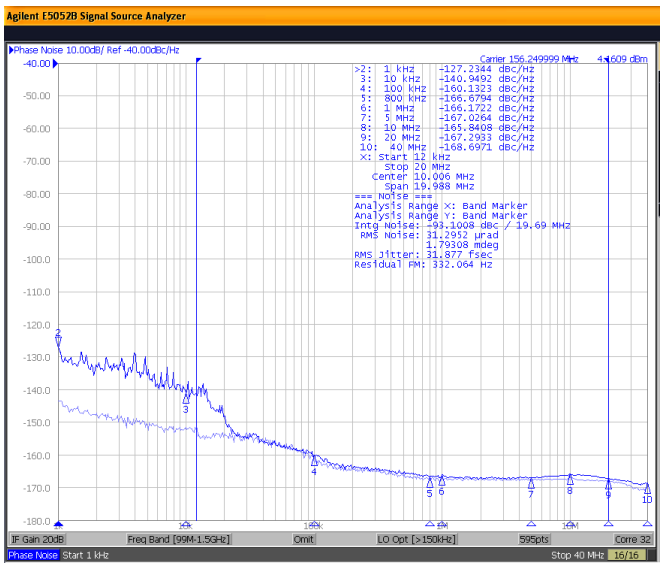


图 13. LMK1C110x 1.8-V Output Phase Noise 32-fs (12 kHz to 20 MHz)

10 Power Supply Recommendations

High-performance clock buffers can be sensitive to noise on the power supply, which may dramatically increase the additive jitter of the buffer. Thus, it is essential to manage any excessive noise from the system power supply, especially for applications where the jitter and phase noise performance is critical.

Filter capacitors are used to eliminate the low-frequency noise from the power supply, where the bypass capacitors provide the very low impedance path for high-frequency noise and guard the power supply system against induced fluctuations. These bypass capacitors also provide instantaneous current surges as required by the device and should have low equivalent series resistance (ESR). To properly bypass the supply, the decoupling capacitors must be placed very close to the power-supply terminals, be connected directly to the ground plane, and laid out with short loops to minimize inductance. TI recommends adding as many high-frequency (for example, 0.1 µF) bypass capacitors, as there are supply terminals in the package. TI recommends, but does not require, inserting a ferrite bead between the board power supply and the chip power supply that isolates the high-frequency switching noises generated by the clock buffer; these beads prevent the switching noise from leaking into the board supply. It is imperative to choose an appropriate ferrite bead with very low DC resistance to provide adequate isolation between the board supply and the chip supply, as well as to maintain a voltage at the supply terminals that is greater than the minimum voltage required for proper operation.

图 14 shows this recommended power supply decoupling method.

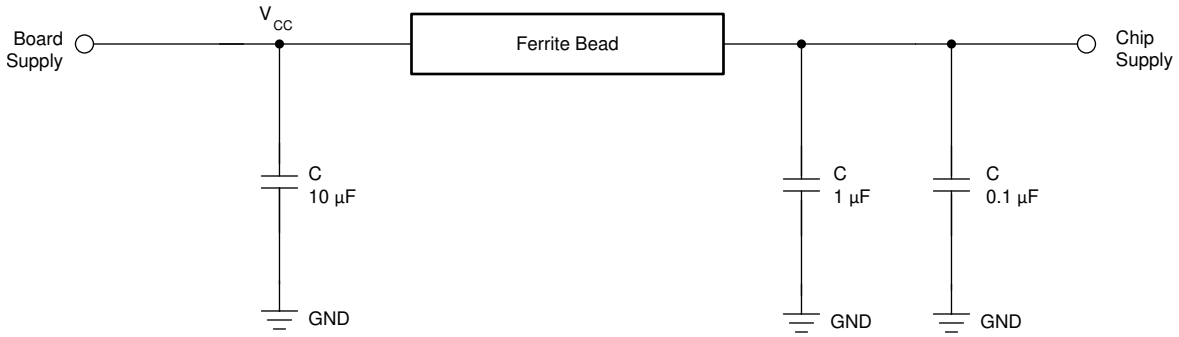


图 14. Power Supply Decoupling

11 Layout

11.1 Layout Guidelines

图 15 shows a conceptual layout detailing recommended placement of power supply bypass capacitors. For component side mounting, use 0402 body size capacitors to facilitate signal routing. Keep the connections between the bypass capacitors and the power supply on the device as short as possible. Ground the other side of the capacitor using a low-impedance connection to the ground plane.

11.2 Layout Example

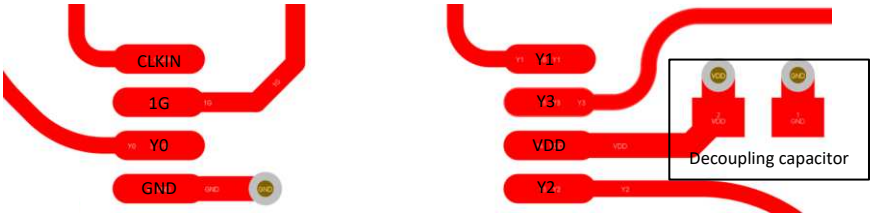


图 15. PCB Conceptual Layout

12 器件和文档支持

12.1 相关链接

下表列出了快速访问链接。类别包括技术文档、支持和社区资源、工具和软件，以及立即订购快速访问。

表 2. 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持和社区
LMK1C1102	单击此处	单击此处	单击此处	单击此处	单击此处
LMK1C1103	单击此处	单击此处	单击此处	单击此处	单击此处
LMK1C1104	单击此处	单击此处	单击此处	单击此处	单击此处

12.2 接收文档更新通知

如需接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的*通知我* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.3 支持资源

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 商标

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMK1C1102DQFR	ACTIVE	WSON	DQF	8	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	L1C2	Samples
LMK1C1102DQFT	ACTIVE	WSON	DQF	8	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	L1C2	Samples
LMK1C1102PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMK1C2	Samples
LMK1C1103PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMK1C3	Samples
LMK1C1104DQFR	ACTIVE	WSON	DQF	8	3000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	L1C4	Samples
LMK1C1104DQFT	ACTIVE	WSON	DQF	8	250	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	L1C4	Samples
LMK1C1104PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMK1C4	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

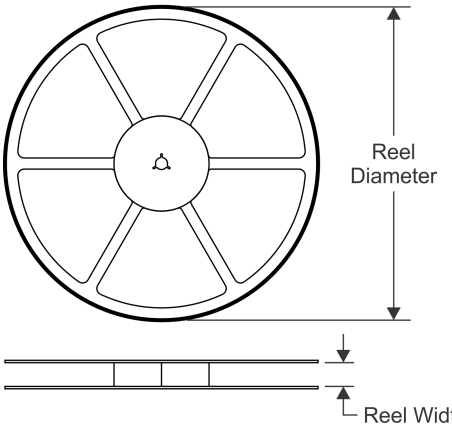
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

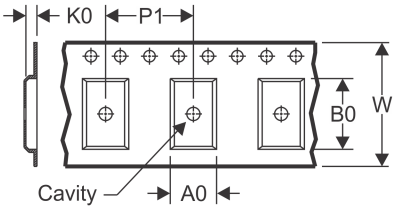
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

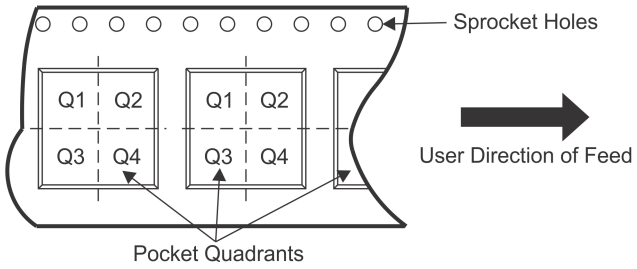


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

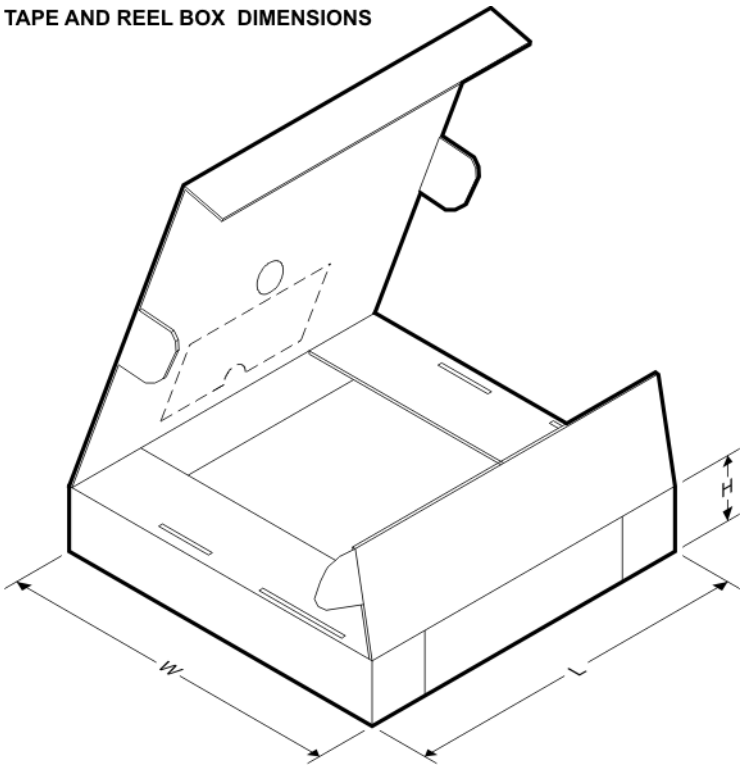
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMK1C1102DQFR	WSON	DQF	8	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
LMK1C1102DQFT	WSON	DQF	8	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
LMK1C1102PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LMK1C1103PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LMK1C1104DQFR	WSON	DQF	8	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
LMK1C1104DQFT	WSON	DQF	8	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
LMK1C1104PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

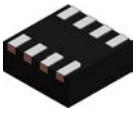


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMK1C1102DQFR	WSON	DQF	8	3000	205.0	200.0	33.0
LMK1C1102DQFT	WSON	DQF	8	250	205.0	200.0	33.0
LMK1C1102PWR	TSSOP	PW	8	2000	853.0	449.0	35.0
LMK1C1103PWR	TSSOP	PW	8	2000	853.0	449.0	35.0
LMK1C1104DQFR	WSON	DQF	8	3000	205.0	200.0	33.0
LMK1C1104DQFT	WSON	DQF	8	250	205.0	200.0	33.0
LMK1C1104PWR	TSSOP	PW	8	2000	853.0	449.0	35.0

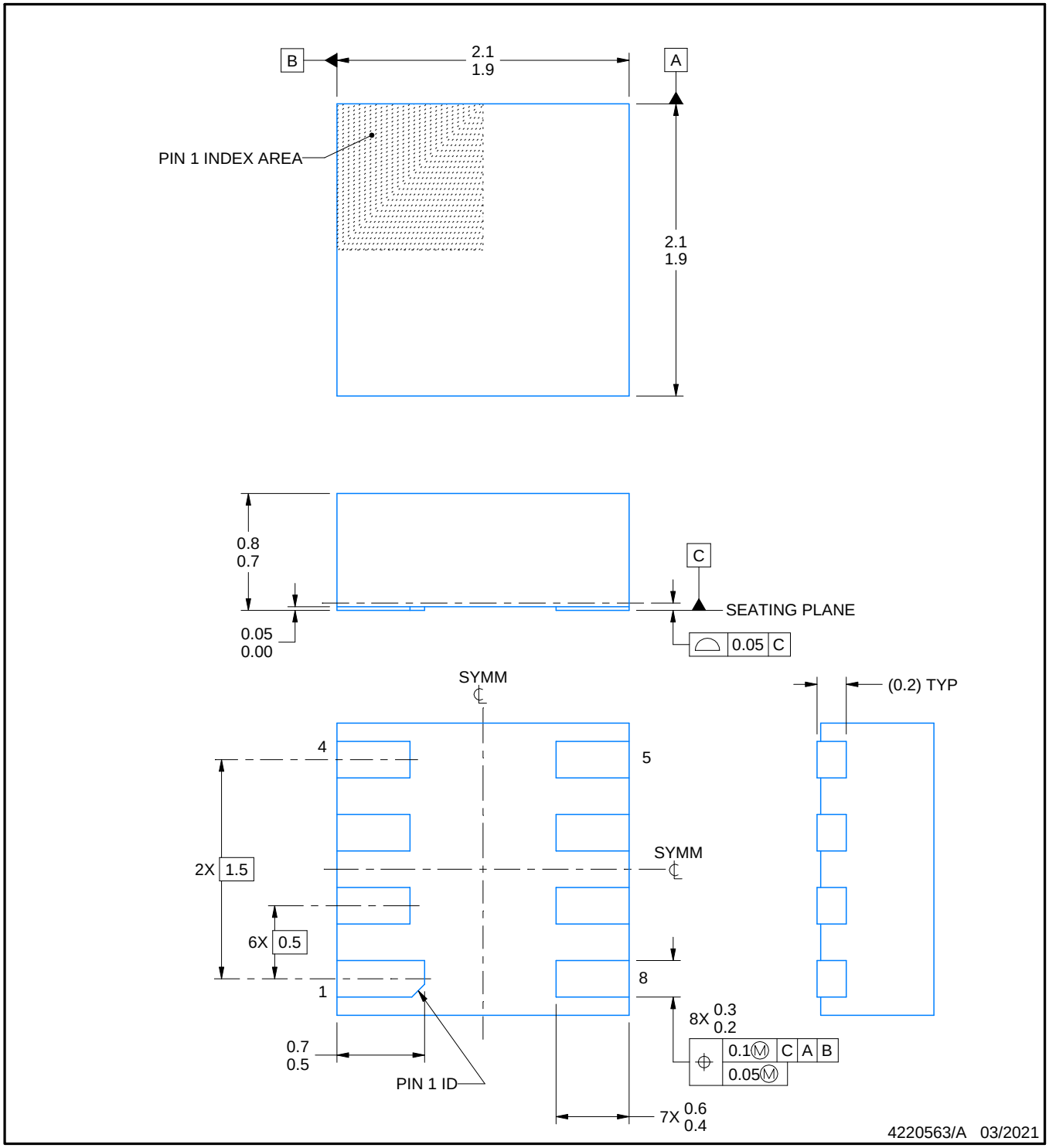
PACKAGE OUTLINE

DQF0008A



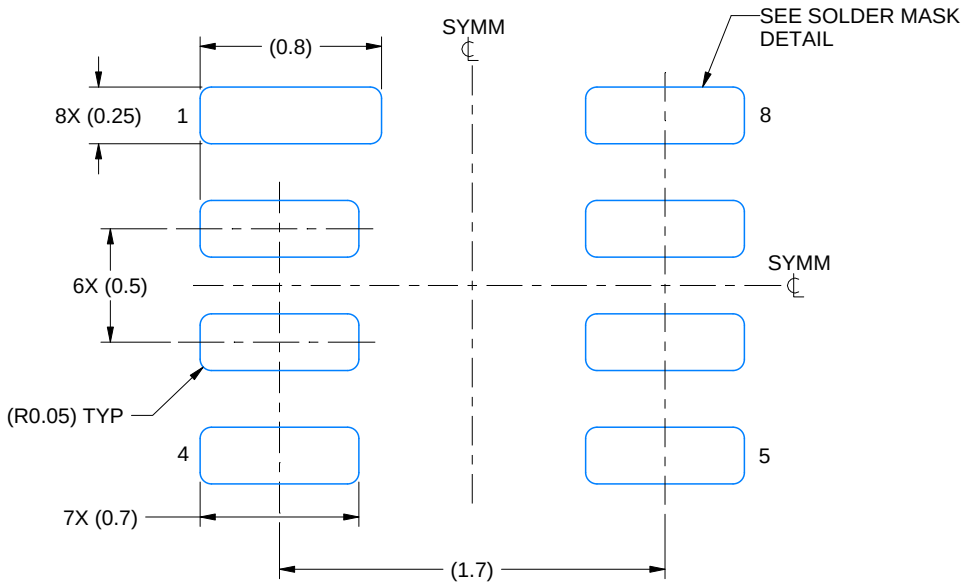
WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

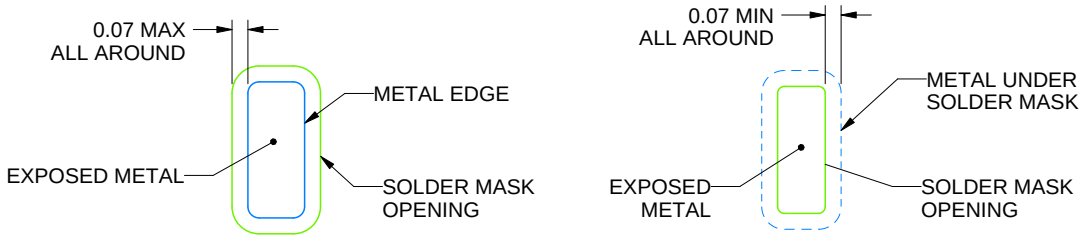


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 30X



SOLDER MASK DETAILS

4220563/A 03/2021

NOTES: (continued)

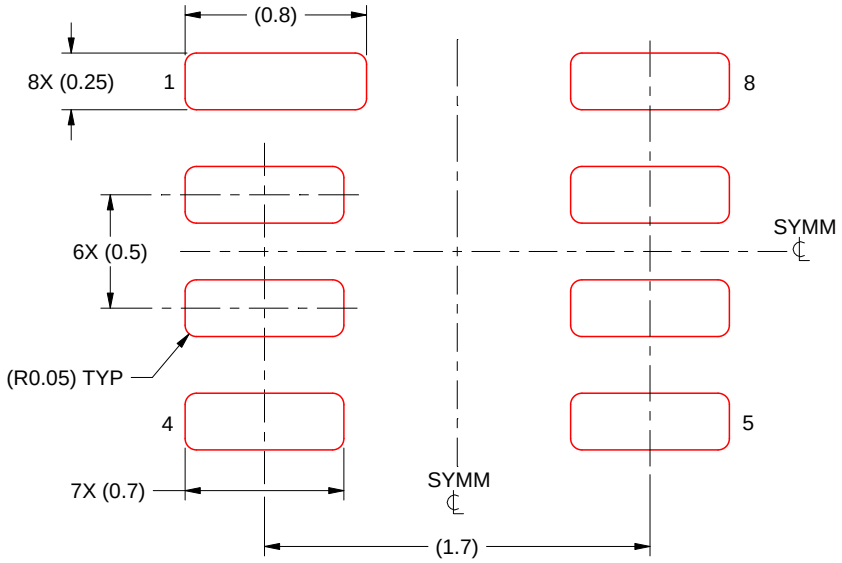
3. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

EXAMPLE STENCIL DESIGN

DQF0008A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 MM THICK STENCIL
SCALE: 30X

4220563/A 03/2021

NOTES: (continued)

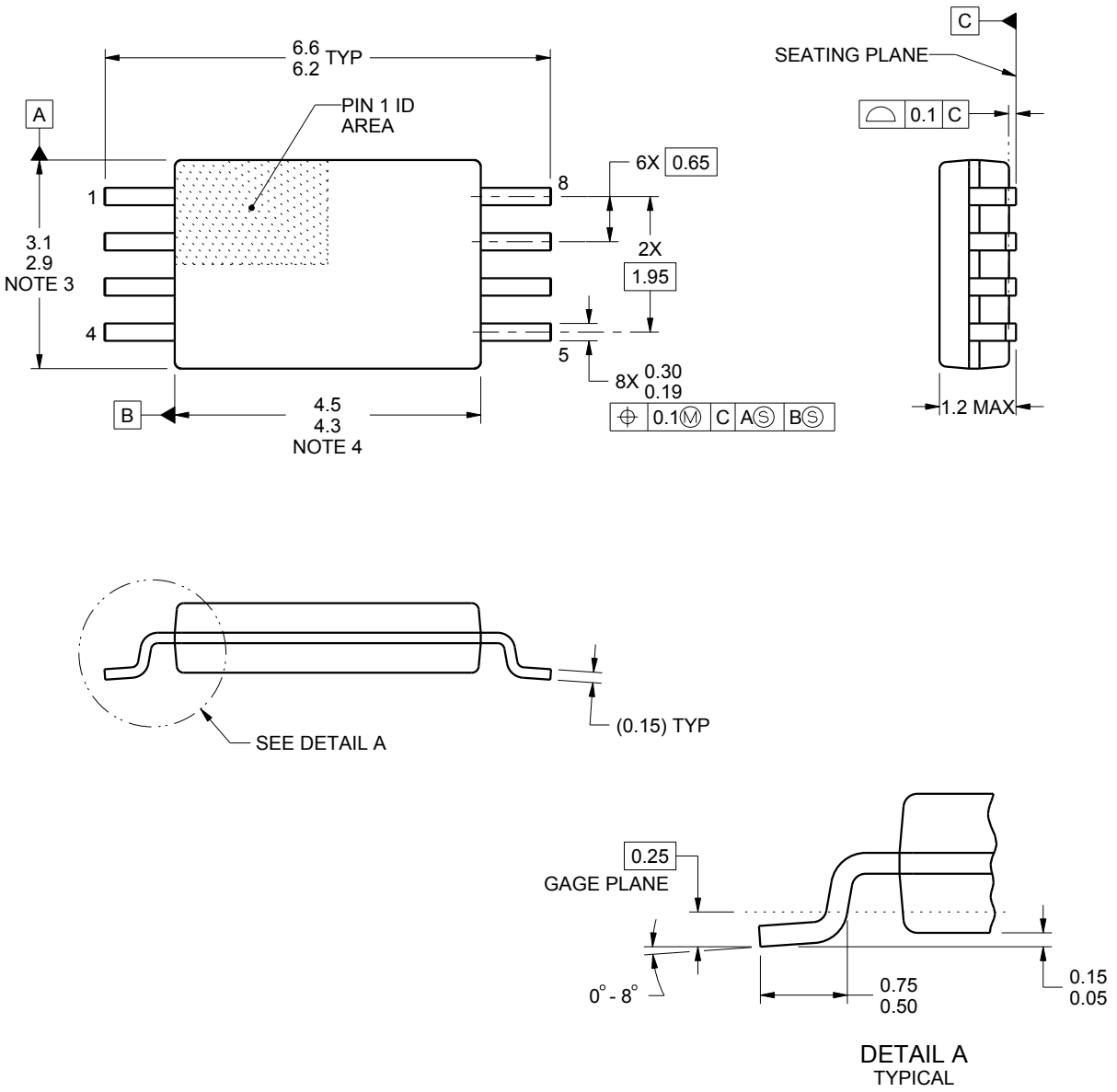
4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGE OUTLINE

PW0008A

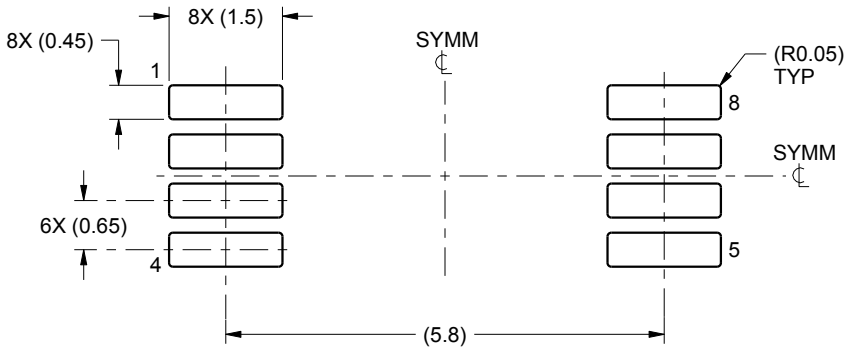
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

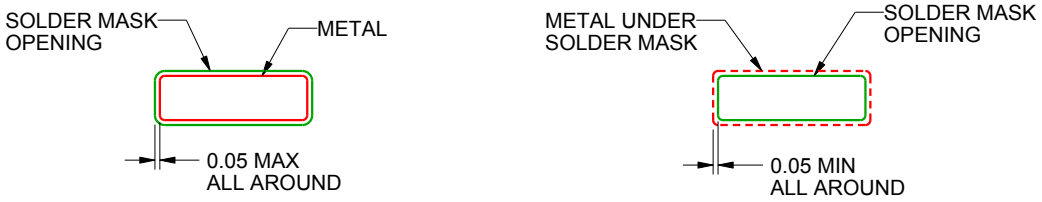


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153, variation AA.



LAND PATTERN EXAMPLE
SCALE:10X

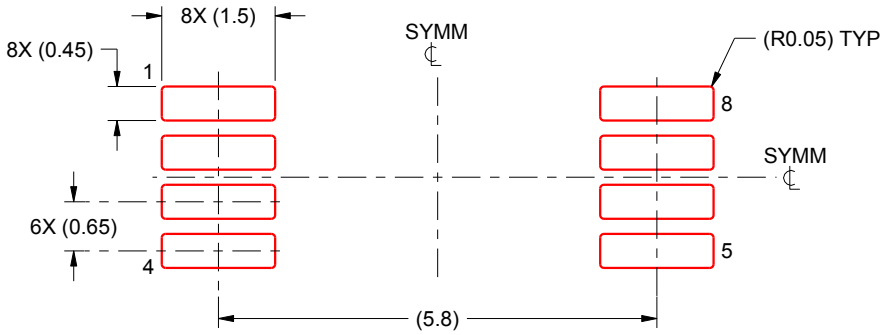


SOLDER MASK DETAILS
NOT TO SCALE

4221848/A 02/2015

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:10X

4221848/A 02/2015

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要声明和免责声明

TI 提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 TI 的销售条款 (https:www.ti.com.cn/zh-cn/legal/termsofsale.html) 或 ti.com.cn 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122